

	Symbol	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	$V_{(BR)DSS}$	100		1.0	V
				5.0	
	I_{GSS}			±100	nA
	$V_{GS(th)}$	1.2	1.9	2.5	V
			8.3	10.0	m
			10.8	13.5	m
	g_{FS}		57		S
	V_{SD}		0.7	1.0	V
	I_S			89	A
		C_{iss}		1535	
	C_{oss}		335		pF
	C_{rss}		8.2		pF
	R_g		1.8		
	Q_g		26		nC
	Q_g		14		nC
	Q_{gs}		4.3		nC
	Q_{gd}		6.8		nC
	$t_{D(on)}$		7.5		ns
	t_r		15.8		ns
	$t_{D(off)}$		31		ns
	t_f		28		ns
	t_{rr}		43		ns
	Q_{rr}		35		nC

Thermal Performance

	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	R_{JA}	42	51	°C/W
Thermal Resistance, Junction-to-Case	R_{JC}	1.1	1.4	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100 \text{ H}$, $V_{GS} = 10\text{V}$, $V_{DD} = 50\text{V}$] while its value is limited by
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence io - Å a ° t g f g f

Typical Electrical & Thermal Characteristics





TO-252-3L Package Information

